



PTO/SB/06a/b (08-03)

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Substitute for form 1449A/B/PTO				Complete if Known	
				Application Number	10/721,488
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)				Filing Date	November 25, 2003
				First Named Inventor	Shiping Guo
				Art Unit	2844 2826
				Examiner Name	Not Yet Assigned Minh-Loan Tran
				Attorney Docket Number	EMCORE 3.0-081
Sheet	1	of	1		

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ³
		Country Code ⁴ -Number-Kind Code ² (if known)				

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NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
MLT	CA	Yanagihara, et al., "Development of GaN-Based Electronic Device on Si", Sanken Technical Report, Vol. 35, No. 1 (2003), pp. 11-14, Japan (English - language translation of Japanese - language publication).	

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¹ Applicant's unique citation designation number (optional). ² Applicant is to place a check mark here if English language Translation is attached.

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Examiner Signature	Minhloan Tran	Date Considered	8/05
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Sheet	1	of	2
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		Number-Kind Code ² (if known)			
MLT	AA	US-2003/0015708-A1	01-23-2003	Parikh, et al.	
	AB	US-2003/0062525-A1	04-03-2003	Parikh, et al.	
	AC	US-2003/0075728-A1	04-24-2003	Tool, et al.	
	AD	US-5,158,909-B1	10-27-1992	Ohtsuka, et al.	
	AE	US-5,602,418-B1	02-11-1997	Imai, et al.	
	AF	US-5,622,877-B1	04-22-1997	Ashkinazi, et al.	
	AG	US-5,877,558-B1	03-02-1999	Nakamura, et al.	
	AH	US-5,956,578-B1	09-21-1999	Weitzel, et al.	
	AJ	US-6,255,198-B1	07-03-2001	Linthicum, et al.	
	AJ	US-6,323,053-B1	11-27-2001	Nishikawa, et al.	
	AK	US-6,507,041-B1	01-14-2003	Nakamura, et al.	
	AL	US-6,524,900-B1	02-25-2003	Dahlgvist, et al.	
	AM	US-6,576,973-B1	06-10-2003	Collard, et al.	
	AN	US-6,586,777-B1	07-01-2003	Yuasa, et al.	
	AO	US-6,586,781-B1	07-01-2003	Wu, et al.	
	AP	US-6,602,764-B1	08-05-2003	Linthicum, et al.	
	AQ	US-6,608,327-B1	08-19-2003	Davis, et al.	
	AR	US-6,610,995-B1	08-26-2003	Nakamura, et al.	
MLT	AS	US-6,437,374-B1	08-20-2002	Northrup, et al.	

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		Country Code ² -Number ² -Kind Code ² (if known)				
MLT	BA	-WO 02/48434 A2	06-20-2002	Nitronex Corporation		
MLT	BB	-DE 4210402	10-01-1992	Koichi		
MLT	BC	-EP 0 380 340	04-29-1992	Cree Research Inc.		

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NON PATENT LITERATURE DOCUMENTS

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MLT	CA	Brown, et al., "AlGaIn/GaN HFETs Fabricated on 100-mm GaN on Silicon (111) Substrates," Solid-State Electronics, Vol. 46, pp. 1535-1539 (2002)	
	CB	Feltin, et al., "Stress Control in GaN Grown on Silicon (111) by Metalorganic Vapor Phase Epitaxy," Applied Physics Letters, Vol. 79, No. 20, pp. 3230-3232 (November 12, 2001)	
	CC	Marchand, et al., "Metalorganic Chemical Vapor Deposition of GaN on Si (111): Stress Control and Application to Field-Effect Transistors," Journal of Applied Physics, Vol. 89, No. 12, pp. 7846-7851 (June 15, 2001)	
	CD	Armitage, et al., "Lattice-Matched HfN Buffer Layers for Epitaxy of GaN on Si," Applied	

Examiner Signature	Minhloan Tran	Date Considered	8/05
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Sheet	2	of	2	Attorney Docket Number	EMCORE 3.0-081

MLT		Physics Letters, Vol. 81, No. 8, pp. 1450-1452 (August 15, 2002)	
	CE	Manohar, et al., "Characteristics of Microwave Power GaN HEMTs on 4-inch Si Wafers," 2002 IEEE International Microwave Symposium, Seattle WA	
	CF	Kalisch, et al., "Growth and Characterisation of AlGaIn/GaN HEMT on Silicon Substrates"	
	CG	Dadgar, et al., "MOVCD Grown AlGaIn/GaN FETs on Si(111)"	
	CH	Poschenrieder, et al., "Bright Blue to Orange Photoluminescence Emission from High-Quality InGaIn/GaN Multiple-Quantum-Wells on Si(111) Substrates," Applied Physics Letters, Vol. 81, No. 9, pp. 1591-1593 (August 26, 2002)	
	CI	Jang, et al., "Characteristics of GaN/Si(111) Epitaxy Grown Using Al _{0.1} Ga _{0.9} N/AlN Composite Nucleation Layers Having Different Thicknesses of AlN," Journal of Crystal Growth, Vol. 241, pp. 289-296 (2002)	
	CJ	Wan, et al., "Growth of Crack-Free Hexagonal GaN Films on Si(100)," Applied Physics Letters, Vol. 79, No. 10, pp. 1459-1461 (September 3, 2001)	
	CK	Tran, et al., "Growth of InGaIn/GaN Multiple-Quantum-Well Blue Light-Emitting Diodes on Silicon by Metalorganic Vapor Phase Epitaxy," Applied Physics Letters, Vol. 75, No. 11, pp. 1494-1496 (September 13, 1999)	
MLT	CL	Dadgar, et al., "Thick, Crack-Free Blue Light-Emitting Diodes on Si(111) Using Low-Temperature AlN Interlayers and <i>In Situ</i> Si ₃ N ₄ Masking," Applied Physics Letters, Vol. 80, No. 20, pp. 3670-3672 (May 20, 2002)	

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